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(54) **PHOTOCATHODE AND METHOD FOR ASSEMBLY**

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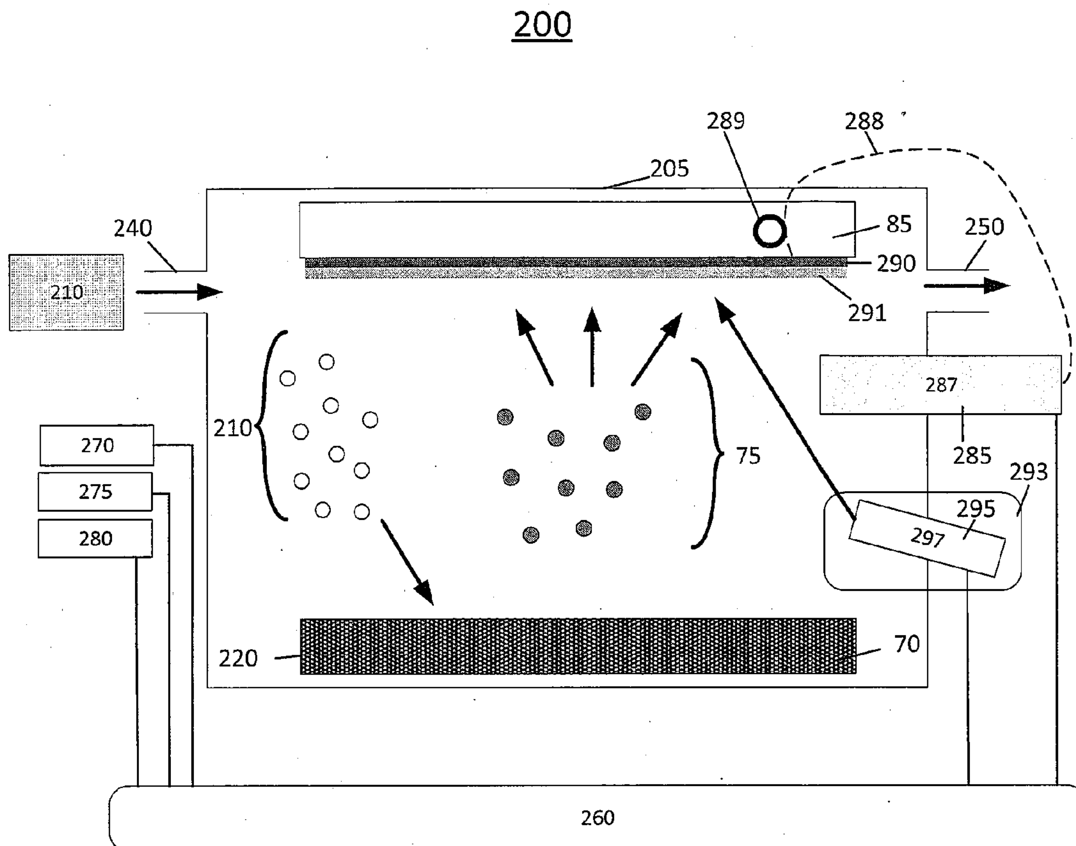
(57) **ABSTRACT**

Technologies are described for methods for fabricating a film component. The methods may comprise sputtering a first film onto a substrate. The first film may include a semiconductor compound material. The semiconductor compound material may include a semi-metal material and one or more alkali material. The methods may further comprise evaporating a second film onto the first film. The second film may include the one or more alkali materials. The one or more alkali materials may catalyze crystallization of the semiconductor compound material in the first film substantially throughout the first film to form the film component in the first layer.



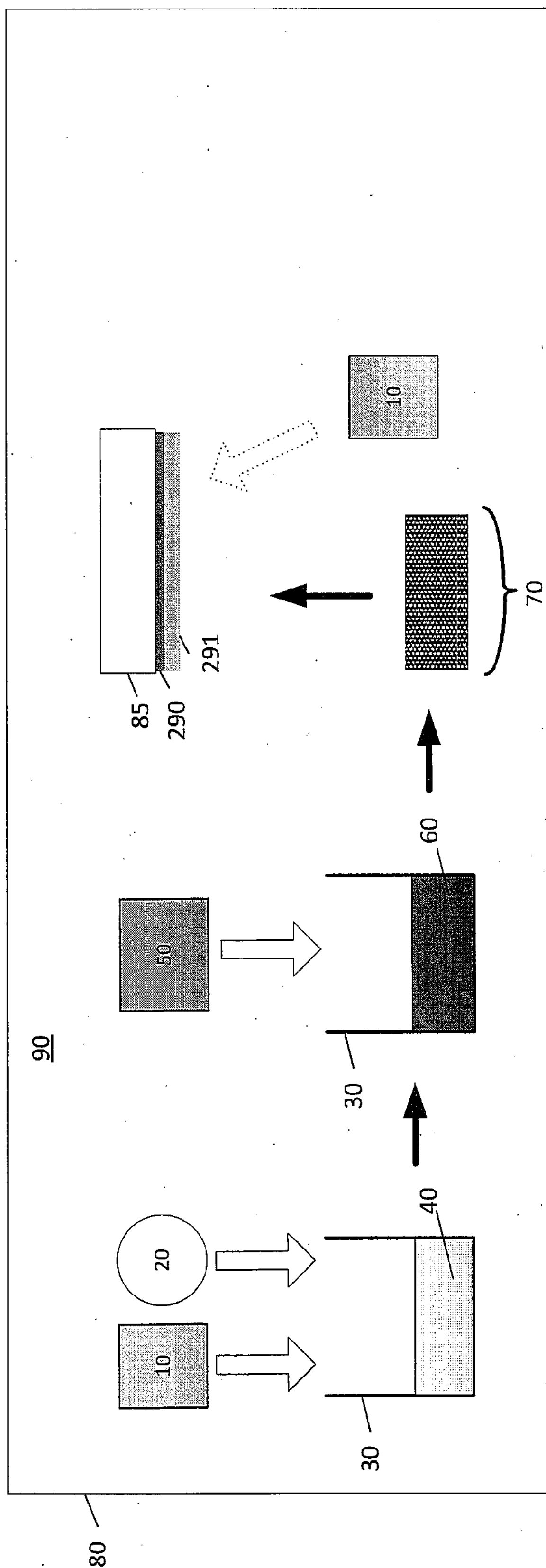


Fig. 1
100
90
10
20
30
40
50
60
70
80
85
290
291

Fig. 2

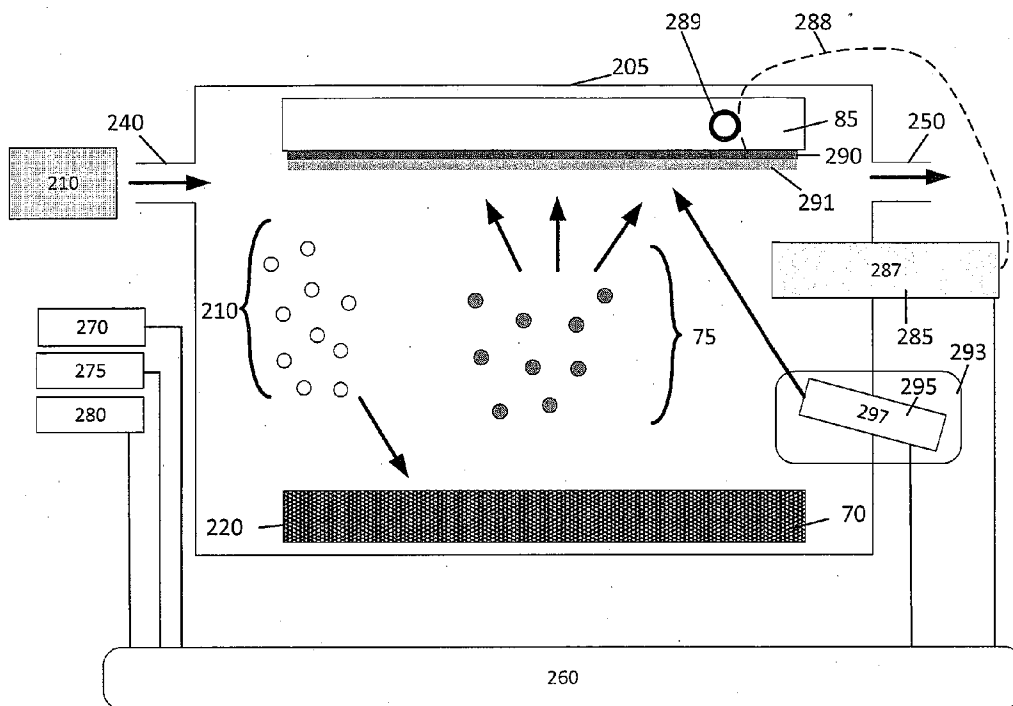
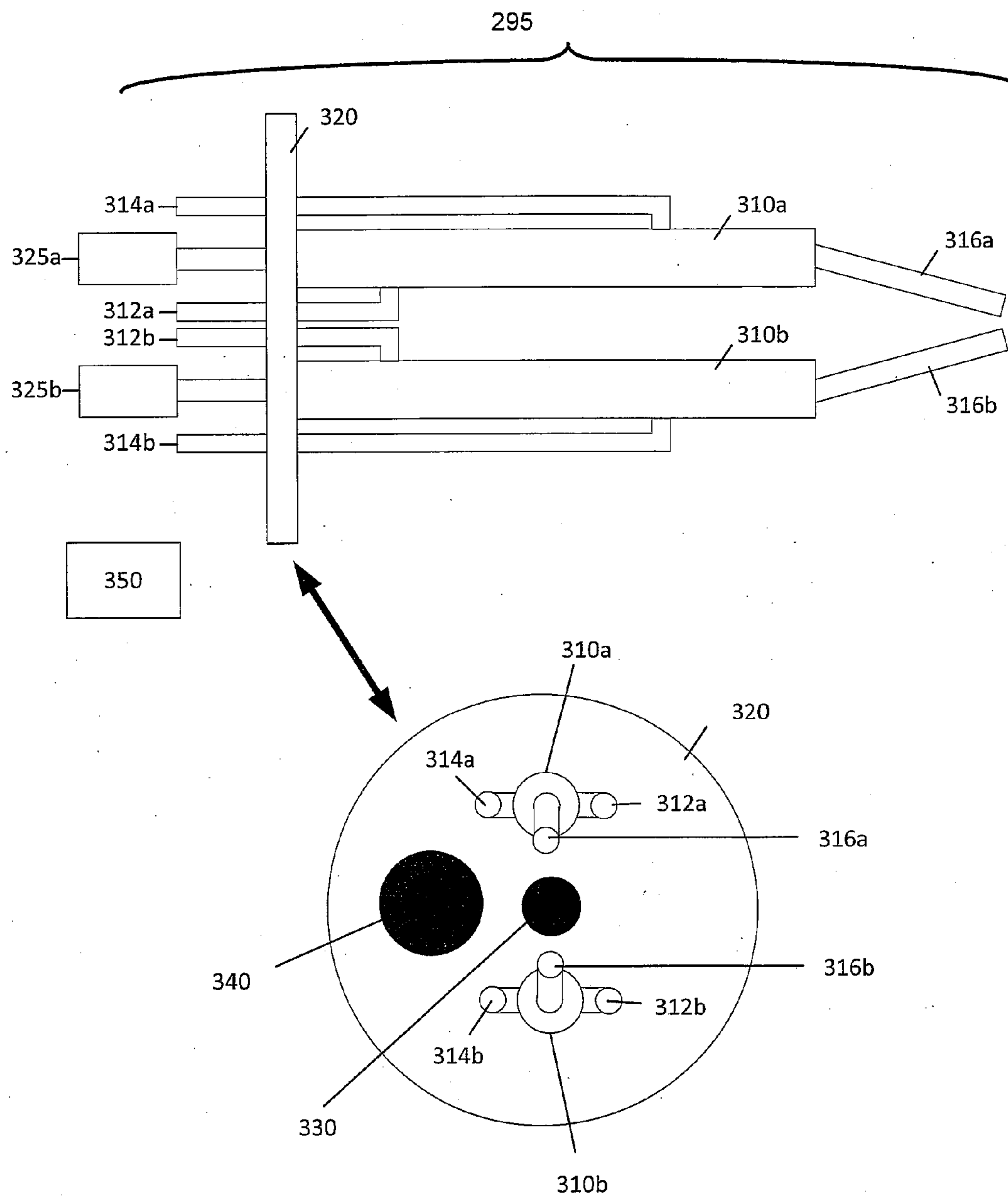


Fig. 3



PHOTOCATHODE AND METHOD FOR ASSEMBLY

CROSS REFERENCE TO RELATED APPLICATION

[0001] This application claims priority to U.S. Provisional Application No. 62/175,125 filed Jun. 12, 2015, the entirety of which is hereby incorporated by reference.

STATEMENT OF GOVERNMENT RIGHTS

[0002] The present invention was made with government support under contract numbers DE-SC0012704 and DE-AC02-05CH11231 awarded by the U.S. Department of Energy. The United States government may have certain rights in this invention.

FIELD OF THE INVENTION

[0003] This disclosure relates generally to alkali antimonide films, photocathodes, and photodetectors.

BACKGROUND

[0004] A photocathode is a metallic or semiconducting cathode that may emit electrons upon the receipt of photons. Alkali antimonide films may be used in photocathodes. Photocathodes may be used in many applications including photodetectors and light sources. A photocathode may be an element in vacuum-tube-based photodetectors, such as discrete-dynode photomultipliers or microchannel-based photomultipliers. A photocathode of a photodetector may dictate the fundamental detector properties including quantum efficiency (QE), wavelength response, dark current behavior, and time response.

SUMMARY

[0005] In some examples, methods for fabricating a film component are generally described. The methods may comprise sputtering a first film onto a substrate. The first film may include a semiconductor compound material. The semiconductor compound material may include a semi-metal material and one or more alkali material. The methods may further comprise evaporating a second film onto the first film. The second film may include the one or more alkali materials. The one or more alkali materials may catalyze crystallization of the semiconductor compound material in the first film substantially throughout the first film to form the film component in the first film.

[0006] In some examples, apparatus effective to fabricate a film component are described. The apparatus may comprise a sputtering device. The sputtering device may be configured to sputter a film of a semiconductor compound material onto a substrate from a target. The target may include the semiconductor compound material. The semiconductor compound material may include a semi-metal material and one or more alkali materials. The apparatus may further comprise an evaporator. The evaporator may be in operative relationship with the sputtering device. The evaporator may be effective to evaporate one or more alkali materials onto the film of the semiconductor compound material to form a layer of the one or more alkali materials. The layer of the one or more alkali materials may catalyze crystallization of the semiconductor compound material in the film substantially throughout the film of the semiconductor compound material.

[0007] In some examples, methods to fabricate a component are generally described. The methods may comprise sputtering a film onto a substrate. The film may include a semiconductor compound material. The semiconductor compound material may include a semi-metal material and one or more alkali materials. The methods may comprise attaching a first material that includes a first alkali on a first end of a first tube. The first tube may be attached to a flange. The methods may comprise attaching a second material that includes a second alkali on a first end of a second tube. The second tube may be attached to the flange. The methods may comprise heating the first tube to evaporate the first material onto the film. The methods may comprise heating the second tube to evaporate the second material onto the film. The methods may comprise depositing the first material from a second end of the first tube onto the film. The methods may comprise depositing the second material from a second end of the second tube onto the film to fabricate the component.

[0008] The foregoing summary is illustrative only and is not intended to be in any way limiting. In addition to the illustrative aspects, embodiments, and features described above, further aspects, embodiments, and features will become apparent by reference to the drawings and the following detailed description.

BRIEF DESCRIPTION OF THE FIGURES

[0009] The foregoing and other features of this disclosure will become more fully apparent from the following description and appended claims, taken in conjunction with the accompanying drawings. Understanding that these drawings depict only several embodiments in accordance with the disclosure and are, therefore, not to be considered limiting of its scope, the disclosure will be described with additional specificity and detail through use of the accompanying drawings, in which:

[0010] FIG. **1** is a system drawing illustrating a synthesis of a semiconductor compound of polycrystalline K_2CsSb;

[0011] FIG. **2** is a system drawing illustrating a sputtering and evaporating apparatus effective to fabricate a crystallized alkali semi-metallic film photocathode; and

[0012] FIG. **3** is a drawing illustrating an evaporating apparatus effective to fabricate a crystallized alkali semi-metallic film photocathode;

[0013] all arranged according to at least some embodiments described herein.

DETAILED DESCRIPTION

[0014] In the following detailed description, reference is made to the accompanying drawings, which form a part hereof In the drawings, similar symbols typically identify similar components, unless context dictates otherwise. The illustrative embodiments described in the detailed description, drawings, and claims are not meant to be limiting. Other embodiments may be utilized, and other changes may be made, without departing from the spirit or scope of the subject matter presented herein. It will be readily understood that the aspects of the present disclosure, as generally described herein, and illustrated in the Figures, can be arranged, substituted, combined, separated, and designed in

a wide variety of different configurations, all of which are explicitly contemplated herein.

[0015] As used herein, any compound, material or substance which is expressly or implicitly disclosed in the specification and/or recited in a claim as belonging to a group or structurally, compositionally and/or functionally related compounds, materials or substances, includes individual representatives of the group and all combinations thereof.

[0016] FIG. **1** is a system drawing illustrating a synthesis of a semiconductor compound of polycrystalline K_2CsSb, arranged in accordance with at least some embodiments presented herein. System **100** may include a glove box **80** and a chamber **30**. Glove box **80** may contain an atmosphere **90**. Atmosphere **90** may be argon or other noble gas that has been purified so as to include less than 0.5 ppm of a combination of O_2 and H_2O. An alkali **10** and an alkali **20** may be mixed together in chamber **30**. Alkalis **10** and **20** may be a chemical material from Group **1** of the periodic table. Alkali **10** may be cesium (Cs) and alkali **20** may be potassium (K). Alkali **10** and alkali **20** may be mixed together in chamber **30** to form a liquid alloy composition **40**. In the example shown, liquid alloy composition **40** may be K_2Cs when alkali **10** is Cs and alkali **20** is K. Although the atomic radii of K and Cs may differ by ~14%, K and Cs may form a miscible liquid alloy composition **40** at room temperature. Liquid alloy composition **40** may have a freezing point of about −90° C. A semi-metal **50** may be added to alloy composition **40** in chamber **30**. Semi-metal **50** may be from Group **1-5** of the periodic table (also referred to as Group Va, the nitrogen group, or the pnictogens). Semi-metal **50** may include arsenic, antimony and bismuth. Semi-metal **50** may be antimony (Sb). Semi-metal **50** may be added to alloy composition **40**. Semi-metal **50** may be one molar proportion of semi-metal **50** and may be added in powder or bead form. Semi-metal **50** may be added to alloy composition **40** to form semiconductor compound **60** at room temperature. Semiconductor **60** may have a conductivity between that of an insulator and that of most metals. Semiconductor compound **60** may be further ground to a fine homogenous powder **70** of semiconductor compound **60** using a mortar and pestle. As discussed in more detail below, powder **70** of semiconductor compound **60** may be deposited on a substrate **85** to form a film **290** of semiconductor compound **60**. A film **291** of alkali **10** may be deposited on film **290** (i.e., a deposit after sputtering or a post-deposition) to catalyze crystallization (or achieve re-crystallization) of semiconductor compound **60** in film **290**.

[0017] In an example, semi-metal **50** may be Sb, and may be added to an alloy composition **40** of alkalis Cs and K, to complete a reaction of a semiconductor compound **60** of alkali antimonide (K_2CsSb), at room temperature. The reaction to form semiconductor compound **60** of alkali antimonide (K_2CsSb) may be spontaneous at room temperature and may occur with a release of some heat. Semiconductor compound **60** of alkali antimonide (K_2CsSb) may be a black-colored, highly crystalline powder. Semiconductor compound **60** of alkali antimonide (K_2CsSb) may be ground to fine homogenous powder **70** of semiconductor compound **60** comprising alkali antimonide (K_2CsSb) using mortar and pestle. Powder **70** may comprise a powder of semiconductor compound **60** of alkali antimonide (K_2CsSb) and may be a nanocrystalline powder whose crystallites measure 15-30 nm.

[0018] FIG. **2** is a system drawing illustrating a sputtering and evaporating apparatus effective to fabricate a crystallized alkali semi-metallic film photocathode, all arranged in accordance with at least some embodiments presented herein. Those components in FIG. **2** that are labeled identically to components of FIG. **1** will not be described again for the purposes of clarity. System **200** may include a chamber **205** with an inlet **240** and an outlet **250**, a sputtering gas **210**, a controller **260**, an X-ray florescence detector **270**, an X-ray powder refraction detector **275**, an X-ray reflectivity detector **280**, a QE measuring device **285**, and an evaporator **295**. Controller **260** may be in communication with X-ray florescence detector **270**, X-ray powder refraction detector **275**, X-ray reflectivity detector **280**, QE measuring device **285**, and evaporator **295**. Evaporator **295** may be a device capable of emission of alkali metal upon heating. Evaporator **295** may be a thermal evaporation apparatus, an e-beam evaporator apparatus, or a hot wall evaporation apparatus. Evaporator **295** may be in a separate chamber **293**. Chamber **293** may protect and store evaporator **295** during sputtering.

[0019] A target **220** may be placed within chamber **205**. Target **220** may include powder **70** of semiconductor compound **60** loaded onto a target holder. Powder **70** of semiconductor compound **60** may include alkali antimonide (K_2CsSb) and may be pressed and packed in a film to form target **220**. A tin or Sb layer may be deposited on top of the film of powder **70** of semiconductor compound **60** when preparing target **220** and subsequently removed when target **220** is to be used.

[0020] Substrate **85** may be placed within chamber **205**, opposite to target **220**. Substrate **85** may be silicon and may be cleaned by dipping in dilute hydrofluoric acid and baked to 500° C. prior to placing within chamber **205** for sputtering. Substrate **85** may be held at 120° C. Chamber **205** may have a pressure of 20 mTorr and may contain an argon atmosphere.

[0021] Sputtering gas **210** may be pumped into chamber **205**. Sputtering gas **210** may be a noble gas. Sputtering gas **210** may be neon or argon. Sputtering gas **210** may include energetic particles which may bombard target **220**. Target **220** may be powered to about 10 watts to form plasma. Sputtering gas **210** may dislodge molecules **75** from target **220**. Molecules **75** may include powder **70** comprising semiconductor compound **60**. Semiconductor compound **60** may include alkali antimonide (K_2CsSb). Molecules **75** dislodged from target **220** may deposit on substrate **85** to form film **290**. Film **290** may form at a sputtering rate of 2 angstroms per second (Å/s). Film **290**, formed from molecules **75** may include powder **70** comprising semiconductor compound **60**. Film **290** may be monitored during sputtering of film **290** by in-situ X-ray florescence detector **270**, in-situ X-ray powder refraction detector **275**, and/or in-situ QE measuring device **285**. X-ray florescence detector **270** may detect stoichiometry for semiconductor compound **60**. X-ray powder refraction detector **275** may detect crystallization of semiconductor compound **60**. For example, X-ray powder refraction detector **275** may detect that film **290** has a crystalline structure that is crystallized substantially throughout the thickness of film **290**.

[0022] QE measuring device **285** may include a light source **287**, a lead **288**, and an anode **289**. QE measuring device **285** may determine a ratio between photons incident upon film **290** to photons converted into electrons by film

290. QE measuring device may apply an electric bias between anode **289** coupled by lead **288** to film **290**. Anode **289** may be a metallic ring and may be proximate to film **290** and remote from layer **291**. Light source **287** may be a single wavelength light source or a wide band light source. Light source **287** may emit light of a wavelength incident to film **290**. QE device **285** may measure a photocurrent produced by film **290** in response to incident light from light source **287**. QE measuring device **285** may measure photocurrent produced by film **290** between anode **289** and film **290**. QE measuring device may determine a QE of film **290** based on the measured photocurrent and the wavelength. In an example, over the course of production of film **290**, a QE of about 0.001% up to 50% may be determined. Film **290** may be a photocathode.

[0023] After sputtering of film **290**, X-ray reflectivity detector **280** may detect a smoothness of the surface of film **290** by measuring the specular and off-specular reflection of the primary beam from film **290**. Film **290**, formed by sputtering may be smoother than a film formed by another process such as thermal evaporation. Film **290** may be 10 nm to 200 nm in thickness.

[0024] Once sputtering is complete and film **290** is formed to a thickness of about 10 nm-200 nm, evaporator **295** may deposit alkali **297** onto film **290** to form layer **291**. Alkali **297** may be a chemical material from Group **1** of the periodic table. Alkali **297** may be cesium (Cs). Alkali **297** may include more than one alkali, and may include cesium (Cs) and potassium (K). Evaporator may heat alkali **297** to a temperature of 70° C. to 130° C. Evaporator **295** may deposit alkali **297** to form layer **291** on film **290** at a rate of 0.1 angstroms per second. X-ray florescence detector **270** may detect stoichiometry for semiconductor compound **60** while evaporator **295** is depositing layer **291** of alkali **297** onto film **290**. X-ray powder refraction detector **275** may detect crystallization of semiconductor compound **60** while evaporator **295** is depositing layer **291** of alkali **297** to film **290**. QE detector **285** may determine QE of film **290** while evaporator **295** is depositing layer **291** of alkali **297** to film **290**. In an example where film **290** includes alkali antimonide (K_2CsSb), X-ray florescence detector **270** may detect stoichiometry of alkali antimonide (K_2CsSb), X-ray powder refraction detector **275** may detect crystallization of alkali antimonide (K_2CsSb), and/or QE detector **285** may determine QE of film **290** of alkali antimonide (K_2CsSb).

[0025] Controller **260** may control evaporator **295** to deposit layer **291** of alkali **297** onto film **290**. Controller may control evaporator **295** to deposit layer **291** of alkali **297** until controller **260** determines that the stoichiometry of semiconductor compound **60** is acceptable. Stoichiometry of semiconductor compound **60** may be detected by X-ray florescence detector **270** in communication with controller **260**. X-ray florescence detector **270** may incident semiconductor compound **60** with incident X-ray light. Semiconductor compound **60** may emit X-ray light at a lower energy than the incident X-ray light in response. X-ray florescence detector **270** may detect the X-ray light emitted from semiconductor material **60** and identify characteristics of the emitted X-ray light including peak heights to identify elements and a quantity of elements in semiconductor compound **60**. Controller **260** may control evaporator **295** to deposit layer **291** of alkali **297** until the crystallization of compound **60** in film **290** has a crystalline structure that is crystallized substantially throughout the thickness of film **290**. Crystallization of film **290** may be detected by X-ray powder refraction detector **275** in communication with controller **260**. Controller **260** may control evaporator **295** to deposit layer **291** of alkali **297** until a QE value for film **290** is detected with a value greater than a threshold value. A QE value of film **290** may be detected by QE detector **285** connected to controller **260**. Controller **260** may control evaporator **295** to deposit film **291** of alkali **297** for a time period of about 30 minutes. Film **291** of alkali **297** deposited by evaporator **295** onto film **290** may catalyze crystallization of semiconductor compound **60**. For example, when semiconductor compound **60** is alkali antimonide (K_2CsSb) and alkali **297** is CS, Cs may catalyze crystallization of alkali antimonide (K_2CsSb) substantially throughout film **290**. Layer **291** may have a thickness of 10 nm to 200 nm. After alkali **297** is deposited by evaporator **295**, film **290** may display good photo response with a peak QE of 12% at 350 nm.

[0026] FIG. **3** is a drawing illustrating an evaporating apparatus effective to fabricate a crystallized alkali semimetallic film photocathode, all arranged in accordance with at least some embodiments presented herein. Those components in FIG. **3** that are labeled identically to components of FIGS. **1-2** will not be described again for the purposes of clarity.

[0027] Evaporator **295** may include hot air intake tubes **314***a*, **314***b*, hot air return tubes **312***a*, **312***b*, heating tubes **310***a*, **310***b*, alkali output tubes **316***a*, **316***b*, and flange **320**. Alkali sources **325***a*, **325***b* may be attached to evaporator **295**. Hot air intake tubes **314***a* and **314***b* may supply hot air to heating tubes **310***a* and **310***b* respectively. Heating tubes **310***a* and **310***b* may surround the outer walls of alkali output tubes **316***a* and **316***b* respectively and may heat alkali within alkali outlet tubes **316***a*, **316***b*. Alkali sources **325***a* and **325***b* may each supply a material to alkali outlet tubes **316***a* and **316***b* respectively. A material supplied by alkali sources **325***a* and **325***b* may be the same alkali, or may be two different alkalis, one from alkali source **325***a* and a second from alkali source **325***b*. Material emitted from evaporator **295** may be 70° C. to 130° C. Material emitted from evaporator **295** may be kept at a constant temperature by an electronic controller **350** which may electronically control the temperature of hot air to hot air intake tubes **314***a* and **314***b*.

[0028] Flange **320** may define a first hole **330** and a second hole **340**. First hole **330** may be a shaft for a shutter. Second hole **340** may allow light to be shown towards the deposition end of evaporator **295**.

[0029] Among other possible benefits, a system in accordance with the present disclosure may provide photocathodes with high quantum efficiency. Sputter deposition in accordance with the present disclosure of a semiconductor compound may produce a smoother photocathode surface (approaching or substantially atomically smooth, with a roughness on the same order as the characteristic length scale between atoms in the material) than a photocathode produced by thermal evaporation. A system in accordance with the present disclosure may improve the quantum efficiency of the sputtering produced photocathode. A system in accordance with the present disclosure may convert the amorphous alkali antimonide of the semiconductor compound into a cubic crystalline phase and provide excess surface alkalization to achieve photo response. Photocathodes produced by in accordance with the present disclosure

may be smoother than those produced by other methods and may display good photo response with high quantum efficiency. In another possible benefit, a system in accordance with the present disclosure may uniformly and quickly coat large areas with the semiconductor compound.

[0030] While various aspects and embodiments have been disclosed herein, other aspects and embodiments will be apparent to those skilled in the art. The various aspects and embodiments disclosed herein are for purposes of illustration and are not intended to be limiting, with the true scope and spirit being indicated by the following claims.

1. A method for fabricating a film component, comprising,
sputtering a first film onto a substrate, wherein the first film includes a semiconductor compound material and the semiconductor compound material includes a semi-metal material and one or more alkali materials; and
evaporating a second film onto the first film, wherein:
the second film includes the one or more alkali materials; and
the one or more alkali materials catalyze crystallization of the semiconductor compound material in the first film substantially throughout the first film to form the film component in the first film.

2. The method of claim **1**, wherein the semi-metal material is antimony.

3. The method of claim **1**, further comprising:
measuring a quantum efficiency of the film component;
detecting a crystalline structure of the film component; and
continuing the evaporating of the second film onto the first film until the quantum efficiency of the film component is measured to be greater than a threshold value or the crystalline structure is detected substantially throughout the thickness of the film component.

4. The method of claim **3** wherein the measuring of the quantum efficiency of the film component comprises:
applying an electric bias between an anode of a quantum efficiency measuring device and the film component;
emitting an incident light of a wavelength incident to the film component; and
measuring a photocurrent produced by the film component in response to the incident light, wherein the photocurrent is measured between the anode and the film component, and the quantum efficiency of the film component is determined by the quantum efficiency measuring device based on the measured photocurrent and the wavelength.

5. The method of claim **1**, wherein the one or more alkali materials comprise a first alkali material of potassium (K), and a second alkali material of cesium (Cs).

6. The method of claim **1** wherein the semi-metal material is antimony, and wherein the semiconductor compound material comprises K_2CsSb.

7. The method of claim **1**, wherein the first film has a thickness of about 10 nm to about 200 nm, and the second film has a thickness of about 10 nm to about 200 nm.

8. The method of claim **1** wherein the one or more alkali materials comprise cesium (Cs).

9. An apparatus effective to fabricate a film component, the apparatus comprising:
a sputtering device configured to sputter a film of a semiconductor compound material onto a substrate from a target, wherein the target includes the semiconductor compound material and the semiconductor compound material includes a semi-metal material and one or more alkali materials;
an evaporator in operative relationship with the sputtering device, the evaporator effective to evaporate one or more alkali materials onto the film of the semiconductor compound material to form a layer of the one or more alkali materials and catalyze crystallization of the semiconductor compound material in the film substantially throughout the film of the semiconductor compound material to form the film component.

10. The apparatus of claim **9**, further comprising a quantum efficiency detector in operative relationship with the evaporator, wherein the quantum efficiency detector comprises:
a light source, wherein the light source is effective to generate an incident light of a wavelength incident to the film component;
an anode; and
a lead coupled between the anode and the film component, wherein the quantum efficiency detector is effective to measure a photocurrent response in the film of the semiconductor compound material to the incident light from the light source to determine a quantum efficiency.

11. The apparatus of claim **10**, wherein the anode comprises a metallic ring.

12. The apparatus of claim **9**, wherein the evaporator is a thermal evaporation apparatus, an e-beam evaporator apparatus, or a hot wall evaporation apparatus.

13. The apparatus of claim **9**, further comprising an X-ray powder refraction detector.

14. The apparatus of claim **9** wherein the one or more alkali materials comprise a first alkali material of potassium (K) and a second alkali material of cesium (Cs).

15. The apparatus of claim **14** wherein the semi-metal material is antimony, and where in the semiconductor compound material comprises K_2CsSb.

16. The apparatus of claim **9** wherein a thickness of the semiconductor compound material is about 10 nm to about 200 nm and a thickness of the layer of the one or more alkali materials is about 10 nm to about 200 nm.

17. The apparatus of claim **9** wherein a thickness of the semiconductor compound material is in a 1:1 ratio with the thickness of the layer of the one or more alkali materials.

18. A method to fabricate a component, the method comprising:
sputtering a film onto a substrate, wherein the film includes a semiconductor compound material and the semiconductor compound material includes a semi-metal material and one or more alkali materials; and
attaching a first material that includes a first alkali on a first end of a first tube, wherein the first tube is attached to a flange;
attaching a second material that includes a second alkali on a first end of a second tube, wherein the second tube is attached to the flange;
heating the first tube to evaporate the first material onto the film;
heating the second tube to evaporate the second material onto the film;
depositing the first material from a second end of the first tube onto the film; and
depositing the second material from a second end of the second tube onto the film to fabricate the component.

19. The method of claim **18** wherein the first tube is surrounded by a first heating tube and the second tube is surrounded by a second heating tube.

20. The method of claim **19**, further comprising controlling, by a controller:

a first flow of first hot air through the first heating tube to heat the first tube; and

a second flow of second hot air through the second heating tube to heat the second material.

* * * * *